



# 11th European Symposium on Semiconductor Detectors

## Wednesday, 10 June 2009

### Defects in Semiconductors and Radiation Tolerance - Main Auditorium (16:40 - 18:20)

time	[id] title	presenter
16:40	[17] Study of the Radiation Hardness of Silicon Sensors for the XFEL	FRETWURST, Eckhart
17:00	[18] Charge collection studies of radiation damaged n- and p-type epitaxial silicon detectors	LANGE, Jörn
17:20	[19] The impact of neutral base region on the collected charge in heavily irradiated silicon detectors	VERBITSKAYA, Elena
17:40	[20] Efficiency of segmented silicon detectors of various thicknesses after hadron irradiations up to $2E16$ n/cm <sup>2</sup>	CASSE, Gianluigi
18:00	[21] Plasma effects in silicon detectors for the European XFEL and their impact on sensor performance	BECKER, Julian